

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 63-227007

(43)Date of publication of application : 21.09.1988

(51)Int.CI.

H01L 21/205

H01L 21/263

(21)Application number : 62-061526

(71)Applicant : MATSUSHITA ELECTRIC IND CO LTD

(22)Date of filing : 17.03.1987

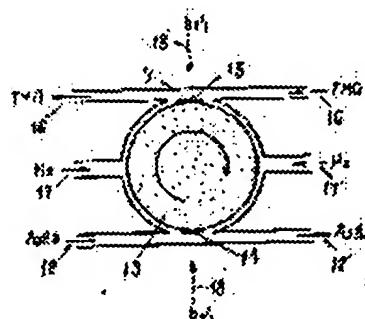
(72)Inventor : TAKAHASHI YASUHITO  
OGURA MOTOTSUGU

## (54) VAPOR GROWTH METHOD

### (57)Abstract:

**PURPOSE:** To obtain a high purity crystal thin film with good reproducibility by feeding reaction gases into a crystal growing chamber with care not to mix each other, and moving a substrate so as to contact the gases to epitaxially grow each atomic layer.

**CONSTITUTION:** A plurality of reaction gases are introduced into a crystal growing chamber, and a crystal thin film is formed on a substrate 15 on a susceptor 13 placed in the chamber 7. Here, the gases are fed with care not to mix each other to a predetermined position in the chamber 7, and the substrate is brought into contact with the gases at the predetermined position to grow the thin film for a predetermined time. Group III and V stock gases are wholly separated to adhere each one layer on the substrate 15, and only the surface ration of the substrate 15 is utilized to eliminate a problem, such as an automatic doping as the growing temperature drops. Thus, a high purity crystal thin film is obtained with good reproducibility.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]